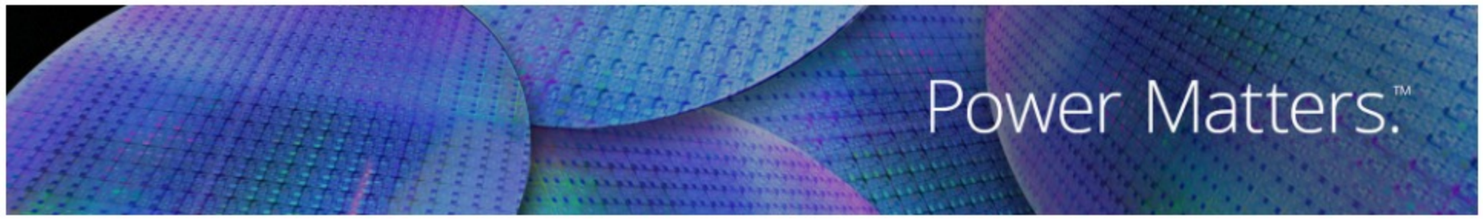
POWER DISCRETES & MODULES

- Voltage & Current Regulation Diodes
- Small Signal Diodes and Diode Arrays
- IGBT
- Power MOSFET
- Power Modules
- JFET
- BJT (BiPolar Junction Transistor)
- Legacy Power Discretes & Modules
- Diode and Rectifier Devices
- Silicon Carbide (SiC) Semiconductor
  - SiC Modules
  - **SiC Schottky Barrier Diodes**
  - SiC MOSFET



Home / Power Discretes & Modules / Silicon Carbide (SiC) Semiconductor / SiC Schottky Barrier Diodes / MSC010SDA170B

MSC010SDA170B

Product Status

In Production

Overview Applications Resources Diagrams Ordering Support

The silicon carbide (SiC) power Schottky barrier diodes (SBD) product line from Microsemi increases your performance over silicon diode solutions while lowering your total cost of ownership for high voltage applications. The MSC010SDA170B is a 1700 V, 10 A SiC SBD in a two-lead TO-247 package.

ROHS

Package Carrier: Tube

Electrical Rating	Symbol	Min	Typ	Max	Unit
Forward Voltage (V)	V_F		1.5	1.8	V

Environmental Rating	Symbol	Min	Typ	Max	Unit
Junction Temperature (°C)	T_J	-55		175	°C

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Forward Current (A)	I_F			10	A
Reverse Breakdown Voltage	V_{BR}			1700	V

This part can be found in the following product categories:

- Power Discretes & Modules ▸ Silicon Carbide (SiC) Semiconductor
- Power Discretes & Modules ▸ Silicon Carbide (SiC) Semiconductor ▸ SiC Schottky Barrier Diodes

© 2019 Microsemi, a wholly owned subsidiary of Microchip Technology Inc. All rights reserved.

Microsemi and the Microsemi logo are registered trademarks of Microsemi Corporation. All other trademarks and service marks are the property of their respective owners.